

# N-Channel 20 V (D-S) MOSFET

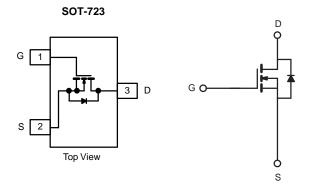
PRODUCT SUMMARY						
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω) Max.	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)			
20	0.300 at V <sub>GS</sub> = 4.5 V	0.9	3.5			
	0.350 at V <sub>GS</sub> = 2.5 V	0.7	5.5			

### FEATURES

- Halogen-free According to IEC 61249-2-21
  Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC

#### **APPLICATIONS**

- Load Switching for Portable Devices
- DC/DC Converter



<b>ABSOLUTE MAXIMUM RATINGS</b> ( $T_A = 25 \text{ °C}$ , unless otherwise noted)						
Parameter		Symbol	5 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	20		V	
Gate-Source Voltage		V <sub>GS</sub>	± 12			
	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	0.9	0.72		
Continuous Drain Current (T <sub>J</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 70 °C		0.68	0.57		
Pulsed Drain Current (t = 300 μs) <sup>b</sup>		I <sub>DM</sub>	3.5		A	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	0.72	0.6		
	T <sub>A</sub> = 25 °C	- P <sub>D</sub>	0.35	0.28	W	
Power Dissipation <sup>a</sup>	T <sub>A</sub> = 70 °C		0.21	0.16		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum lunction to Ambienta	t ≤ 5 s	R <sub>thJA</sub>	120	145		
Maximum Junction-to-Ambient <sup>a</sup>	Steady State		140	175	°C/W	
Maximum Junction-to-Foot	Steady State	R <sub>thJF</sub>	62	78		

Notes:

a. Surface mounted on 1" x 1" FR4 board.

b. Pulse width limited by maximum junction temperature.



COMPLIANT HALOGEN



				Limits			
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{GS}$ = 0 V, $I_D$ = 250 $\mu$ A	20			v	
Gate-Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.50		0.90	v	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V$ , $V_{GS} = \pm 8 V$			± 100	nA	
Zara Cata Valtaga Drain Current	1	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	IDSS	$V_{DS} = 20 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 70 ^{\circ}\text{C}$			75	μA	
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10$ V, $V_{GS} = 4.5$ V	6			А	
		$V_{GS} = 4.5 \text{ V}, \text{ I}_{D} = 0.9 \text{ A}$		0.300		Ω	
Drain-Source On-Resistance <sup>a</sup>	R <sub>DS(on)</sub>	$V_{GS} = 2.5 \text{ V}, \text{ I}_{D} = 0.7 \text{ A}$		0.350			
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 5 \text{ V}, \text{ I}_{D} = 0.9 \text{ A}$		13		S	
Diode Forward Voltage	V <sub>SD</sub>	$I_{\rm S} = 0.95$ A, $V_{\rm GS} = 0$ V		0.7	1.2	V	
Dynamic <sup>b</sup>				•			
Total Gate Charge	Qg			1.5	1.9		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS}$ = 10 V, $V_{GS}$ = 4.5 V, $I_{D}$ = 0.9A		0.25		nC	
Gate-Drain Charge	Q <sub>gd</sub>			0.40			
Gate Resistance	R <sub>g</sub>	f = 1 MHz	2	4	8	Ω	
Switching							
Turn-On Delay Time	t <sub>d(on)</sub>			8	15		
Rise Time	t <sub>r</sub>	$V_{DD}$ = 10 V, $R_L$ = 2.78 $\Omega$		7	15		
Turn-Off Delay Time	t <sub>d(off)</sub>	$\text{I}_{\text{D}}\cong$ 0.9 A, $\text{V}_{\text{GEN}}$ = 4.5 V, $\text{R}_{\text{g}}$ = 1 $\Omega$		30	45	ns	
Fall Time	t <sub>f</sub>			7	15		
Source-Drain Reverse Recovery Time	t <sub>rr</sub>			8.5	15		
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 0.9 A, dl/dt = 100 A/μs			4	nC	

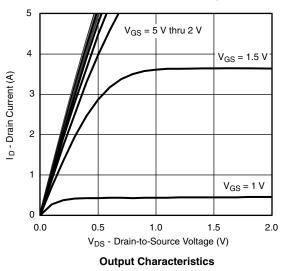
Notes:

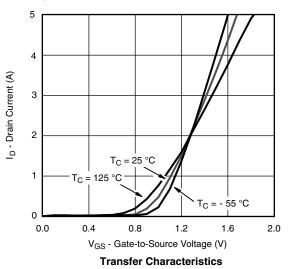
a. Pulse test: Pulse width  $\leq$  300 µs, duty cycle  $\leq$  2 %.

b. Guaranteed by design, not subject to production testing.

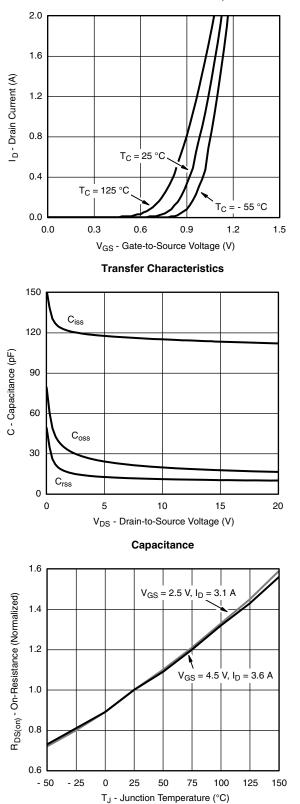
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





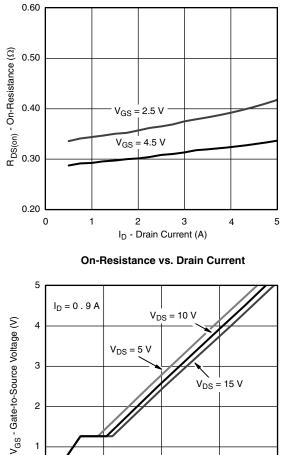






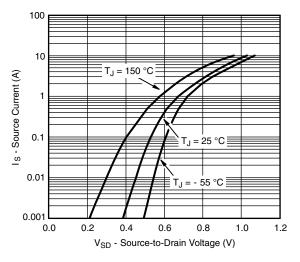
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

On-Resistance vs. Junction Temperature



1 0 0 1 2 3 Q<sub>g</sub> - Total Gate Charge (nC)

**Gate Charge** 

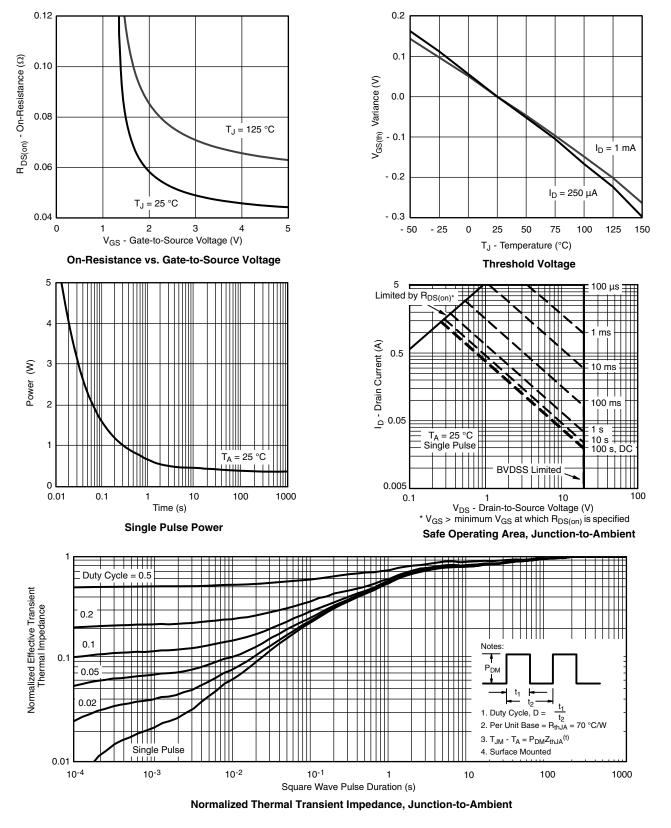


Source-Drain Diode Forward Voltage

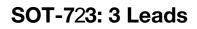
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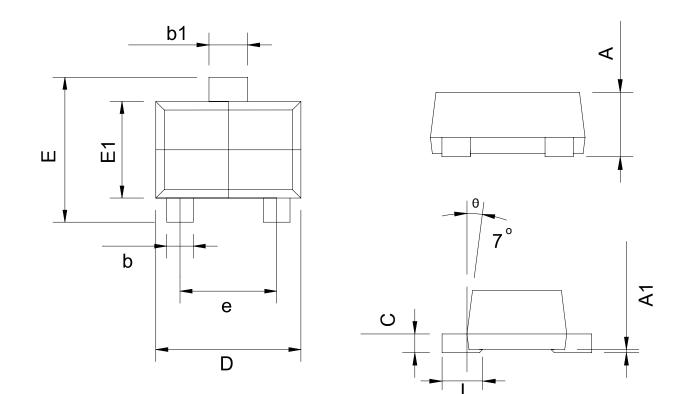


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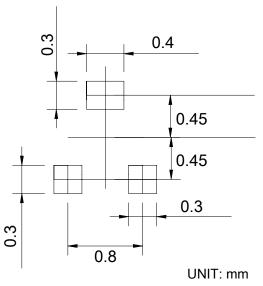






Ş	SOT-723						
SY MBOL	MILLIM	ETERS	INCHES				
	MIN.	MAX.	MIN.	MAX.			
A	-	0.500	-	0.020			
A1	0.000	0.050	0.000	0.002			
b	0.170	0.270	0.007	0.011			
b1	0.270	0.370	0.011	0.015			
с	_	0.150	-	0.006			
D	1.150	1.250	0.045	0.049			
Е	1.150	1.250	0.045	0.049			
E1	0.750	0.850	0.030	0.033			
е	0.800 TYP.		0.031	0.031 TYP.			
L	0.32	BSC	0.013	0.013 BSC			
-	°F	REF.	°R	REF.			







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